

### 100V NPN Darlington transistor in SOT223

#### **Features**

- BV<sub>CEO</sub> > 100V
- BV<sub>CBO</sub> > 100V
- Continuous current I<sub>C(cont)</sub> = 1.5A
- Ultra High Grain

### **Applications**

- Lamp
- Relay
- Solenoid driving

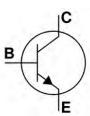
### **Mechanical Data**

- Case: SOT-223
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Matte Tin Finish
- Weight: 0.112 grams (approximate)

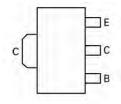
SOT-223



Top View



Device symbol

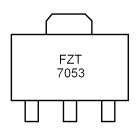


Pin Configuration

## **Ordering Information**

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FZT7053TA	FZT7053	7	12	1000

## **Marking Information**



FZT7053 = Product type Marking Code





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### **Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	100	V
Collector-Emitter Voltage	V <sub>CEO</sub>	100	V
Emitter-Base Voltage	V <sub>EBO</sub>	12	V
Continuous Collector Current	Ic	1.5	Α
Peak Pulse Current	I <sub>CM</sub>	1.8	Α

### **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation at T <sub>A</sub> = 25°C (Note 1) Linear derating factor	P <sub>D</sub>	1.0 8.0	W mW /°C
Power Dissipation at T <sub>A</sub> = 25°C (Note 2) Linear derating factor	P <sub>D</sub>	1.25 10	W mW /°C
Power Dissipation at T <sub>A</sub> = 25°C (Note 3) Linear derating factor	P <sub>D</sub>	6.25 50	W mW /°C
Thermal Resistance, Junction to Ambient (Note 1)	$R_{ hetaJA}$	125	°C/W
Thermal Resistance, Junction to Ambient (Note 2)	$R_{ hetaJA}$	100	°C/W
Thermal Resistance, Junction to Lead (Note 3)	$R_{ heta JL}$	20	°C/W
Operating and Storage Temperature Range	$T_{J}, T_{STG}$	-55 to +150	°C

Notes:

- 1. For a device surface mounted on 15mm X 15mm X 1.6mm FR4 PCB with high coverage of single sided 1 oz copper, in still air conditions
- 2. Mounted on 25mm X 25mm X 1.6mm FR4 PCB with high coverage of single sided 1 oz copper, in still air conditions.
- 3. Junction to lead (collector Tab). Typical.

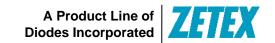
# Electrical Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	100			V	$I_{C} = 100 \mu A$
Collector-Emitter Breakdown Voltage (Note 4)	V <sub>(BR)CEO</sub>	100			V	I <sub>C</sub> = 100mA
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	12			V	$I_E = 100\mu A$
Collector-Base Cutoff Current	I <sub>CBO</sub>		<1	100	nA	V <sub>CB</sub> = 80V
	$0.5$ $\mu$ A $V_{CB} = 3$		$V_{CB} = 80V, T_{amb} = 100^{\circ}C$			
Collector-Emitter Cutoff Current	Ices		<1	200	nA	V <sub>CB</sub> = 80V
Collector-Emiliter Caton Carrent	ICES			0.5	μΑ	$V_{CB} = 80V, T_{amb} = 100^{\circ}C$
Emitter Cutoff Current	I <sub>EBO</sub>		<1	100	. nA	V <sub>EB</sub> = 7V
DC Current Gain (Note 4)	h <sub>FE</sub>	10000 1000				I <sub>C</sub> = 100mA, V <sub>CE</sub> = 5V I <sub>C</sub> = 1A, V <sub>CE</sub> = 5V
Collector-Emitter Saturation Voltage (Note 4)	V <sub>CE(SAT)</sub>			1.5	V	I <sub>C</sub> = 100mA, I <sub>B</sub> = 0.1mA
Base-Emitter Turn-On Voltage (Note 4)	V <sub>BE(ON)</sub>			2.0	mV	I <sub>C</sub> = 100mA, V <sub>CE</sub> = 5V
Output Capacitance (Note 4)	$C_obo$		6.0	8.0	pF	V <sub>CB</sub> = 10V. f = 1MHz
Current Gain-Bandwidth Product (Note 4)	f <sub>T</sub>	200			MHz	$V_{CE} = 5V, I_{C} = 100mA$
Turn-On Time	t <sub>on</sub>		0.7		μs	$V_{CC} = 10V, I_C = 100\mu A$
Turn-Off Time	t <sub>off</sub>		2.5		μs	$I_{B1} = -I_{B2} = 0.1 \text{mA}$

Notes:

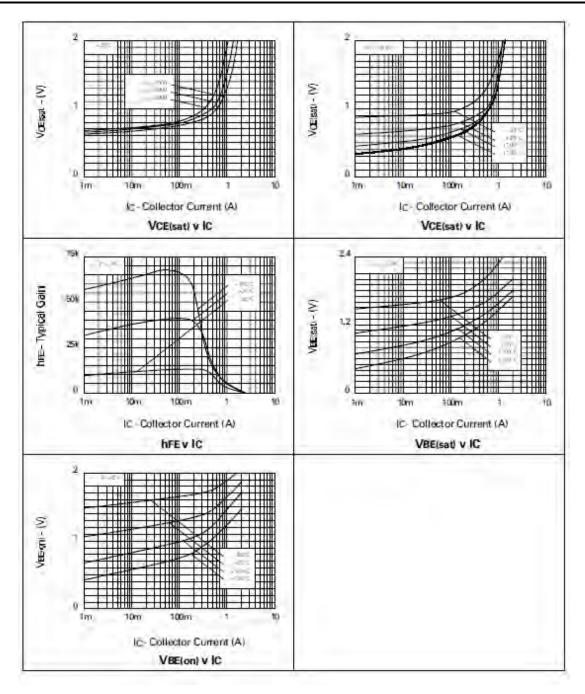
- 1. For a device surface mounted on 15mm X 15mm X 1.6mm FR4 PCB with high coverage of single sided 1 oz copper, in still air conditions 2. Mounted on 25mm X 25mm X 1.6mm FR4 PCB with high coverage of single sided 1 oz copper, in still air conditions.
- 3. Junction to lead (collector Tab). Typical.
- 4. Measured under pulsed conditions. Pulse width = 300 μs. Duty cycle ≤ 2%



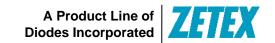


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# **Typical Characteristics**

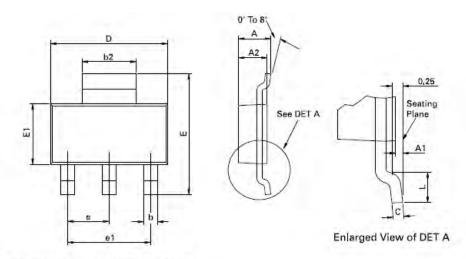






## 100V NPN Darlington transistor in SOT223

# **Package Outline Dimensions**

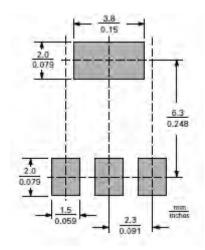


Conforms to JEDEC TO-261 AA Issue B

Dim. Millimeters Min. Ma	illimeters Inch	nes	Millimeters		Inches			
	Max.	Min.	Max.	Dilli.	Min.	Max.	Min.	Max.
CAL	1.80	(4)	0.071	D	6.30	6.70	0.248	0.264
0.02	0.10	0.0008	0.004	е	2.30 BSC		0.0905 BSC	
1.55	1.65	0.0610	0.0649	e1	4.60 BSC		0.181 BSC	
0.66	0.84	0.026	0.033	E	6.70	7.30	0.264	0.287
2.90	3.10	0.114	0.122	E1	3.30	3.70	0.130	0.146
0.23	0.33	0.009	0.013	L	0.90		0.035	
	Min. - 0.02 1.55 0.66 2.90	Min. Max 1.80 0.02 0.10 1.55 1.65 0.66 0.84 2.90 3.10	Min. Max. Min 1.80 - 0.02 0.10 0.0008 1.55 1.65 0.0610 0.66 0.84 0.026 2.90 3.10 0.114	Min.         Max.         Min.         Max.           -         1.80         -         0.071           0.02         0.10         0.0008         0.004           1.55         1.65         0.0610         0.0649           0.66         0.84         0.026         0.033           2.90         3.10         0.114         0.122	Min.         Max.         Min.         Max.           -         1.80         -         0.071         D           0.02         0.10         0.0008         0.004         e           1.55         1.65         0.0610         0.0649         e1           0.66         0.84         0.026         0.033         E           2.90         3.10         0.114         0.122         E1	Min.         Max.         Min.         Max.         Dim.         Min.           -         1.80         -         0.071         D         6.30           0.02         0.10         0.0008         0.004         e         2.30           1.55         1.65         0.0610         0.0649         e1         4.60           0.66         0.84         0.026         0.033         E         6.70           2.90         3.10         0.114         0.122         E1         3.30	Min.         Max.         Min.         Max.         Dim.         Min.         Max.           -         1.80         -         0.071         D         6.30         6.70           0.02         0.10         0.0008         0.004         e         2.30 BSC           1.55         1.65         0.0610         0.0649         e1         4.60 BSC           0.66         0.84         0.026         0.033         E         6.70         7.30           2.90         3.10         0.114         0.122         E1         3.30         3.70	Min.         Max.         Min.         Max.         Min.         Max.         Min.         Max.         Min.           -         1.80         -         0.071         D         6.30         6.70         0.248           0.02         0.10         0.0008         0.004         e         2.30 BSC         0.090           1.55         1.65         0.0610         0.0649         e1         4.60 BSC         0.181           0.66         0.84         0.026         0.033         E         6.70         7.30         0.264           2.90         3.10         0.114         0.122         E1         3.30         3.70         0.130

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

## **Suggested Pad Layout**







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